

2N5961



NPN General Purpose Amplifier

This device is designed for use as low noise, high gain, general purpose amplifiers requiring collector currents to 50 mA. Sourced from Process 07. See 2N5088 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Val60ue	Units	
V_{CEO}	Collector-Emitter Voltage	60	V	
V _{CBO}	Collector-Base Voltage	60	V	
V_{EBO}	Emitter-Base Voltage	8.0	V	
Ic	Collector Current - Continuous	100	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

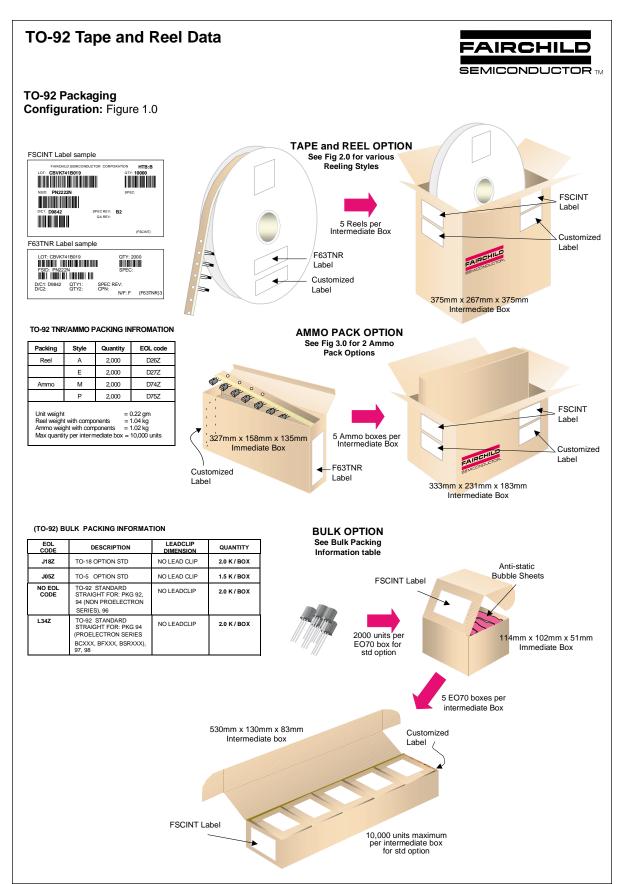
Symbol	Characteristic	Max	Units
		2N5961	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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NPN General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
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o== 0	D. (OTT D. (OTT) O O				
	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 5.0 \text{ mA}, I_B = 0$	60		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, I_E = 0$	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	8.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 45 \text{ V}, I_{E} = 0$		2.0	nA
	Facilities Out of Comment	$V_{CB} = 45 \text{ V}, I_{E} = 0, T_{A} = 65 ^{\circ}\text{C}$		50	nA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$		1.0	nA
ON CHAF	RACTERISTICS*				
h _{FE}	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A}$	100		
- 72		$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$	120		
		$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	135		
		$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$	150	700	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$		0.2	V
		$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}$		0.2	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	0.5	0.7	V
SMALL S	IGNAL CHARACTERISTICS				
C _{cb}	Collector-Base Capacitance	V _{CB} = 5.0 V, f = 1.0 MHz		4.0	pF
C _{eb}	Emitter-Base Capacitance	V _{EB} = 0.5 V, f = 1.0 MHz		6.0	pF
h _{fe}	Small-Signal Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$			
116		f = 1.0 kHz	150	1000	
		$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$			
		f = 100 MHz	1.0		
NF	Noise Figure	$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A},$			
		$R_S = 10 \text{ k}\Omega$, $f = 1.0 \text{ kHz}$,		2.0	40
		$B_W = 400 \text{ Hz}$		3.0	dB
		$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A},$ $R_{S} = 10 k\Omega, f = 10 Hz - 10 k\text{Hz}$			
		$B_W = 15.7 \text{ kHz}$		3.0	dB
		$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A},$		= - =	
		$R_S = 1.0 \text{ k}\Omega$, $f = 1.0 \text{ kHz}$			
				6.0	dB

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

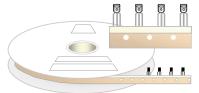


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TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)

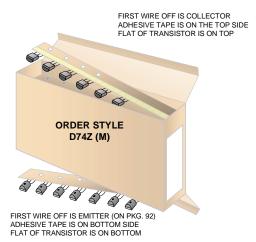


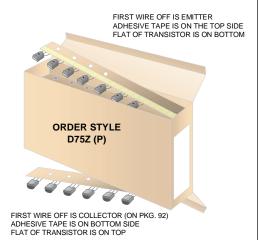
Style "A", D26Z, D70Z (s/h)

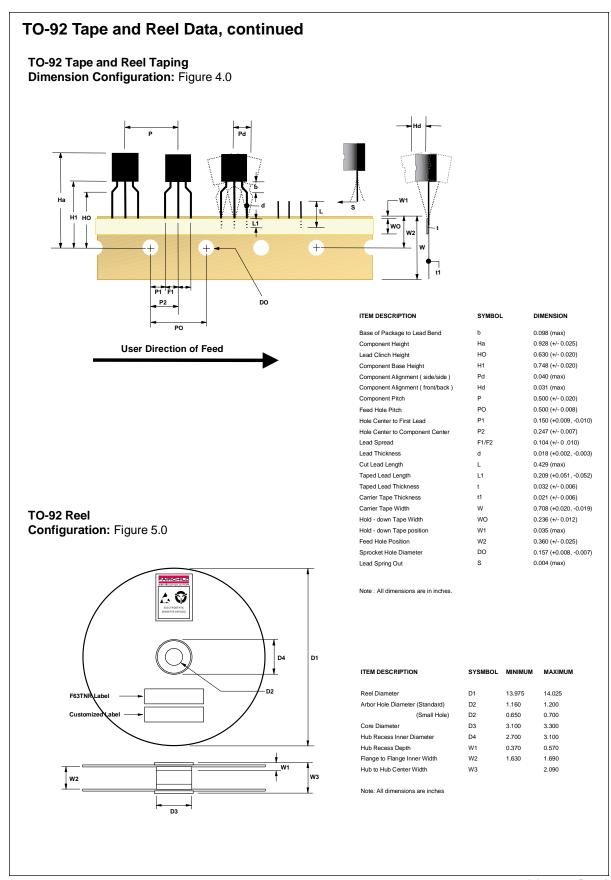
Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0





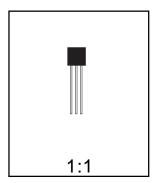


TO-92 Package Dimensions



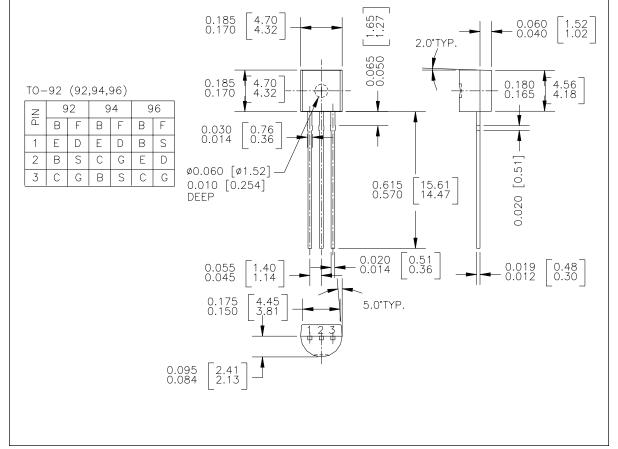
TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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Rev. G